03.10.2022

VISVESVARAYA TECHNOLOGICAL UNIVERSITY, BELAGAVI
B.E: Electronics & Communication Engineering / B.E: Electronics & Telecommunication Engineering
NEP, Outcome Based Education (OBE) and Choice Based Credit System (CBCS)
(Effective from the academic year 2021 – 22)

VI Semester

VLSI Laboratory			
Course Code	**21ECL66**	CIE Marks	50
Teaching Hours/Week (L: T: P: S)	0:0:2:0	SEE Marks	50
Credits	1	Exam Hours	3

Course objectives:

This laboratory course enables students to

- Design, model, simulate and verify digital circuits.
- Design layouts and perform physical verification of CMOS digital circuits.
- Perform ASIC design flow and understand the process of synthesis, synthesis constraints and evaluating the synthesis reports to obtain optimum gate level netlist.
- Perform RTL-GDSII flow and understand the stages in ASIC.

Sl.No.	**Experiments**
	ASIC Digital Design
1	4-Bit Adder • Write Verilog Code • Verify the Functionality using Test-bench • Synthesize the design by setting proper constraints and obtain the netlist. From the report generated identify Critical path, Maximum delay, Total number of cells, Power requirement and Total area required
2	4-Bit Booth Multiplier • Write Verilog Code • Verify the Functionality using Test-bench • Synthesize the design by setting proper constraints and obtain the netlist. From the report generated identify Critical path, Maximum delay, Total number of cells, Power requirement and Total area required
3	32-Bit ALU Supporting 4-Logical and 4-Arithmetic operations, using case and if statement for ALU Behavioral Modeling • Write Verilog Code • Verify functionality using Test-bench • Synthesize the design targeting suitable library and by setting area and timing constraints • Tabulate the Area, Power and Delay for the Synthesized netlist • Identify Critical path
4	Latch and Flip-Flop • Synthesize the design and compare the synthesis report (D, SR, JK)
	ASIC Analog Design
5	a) Capture the schematic of CMOS inverter with load capacitance of 0.1pF and set the widths of Inverter with Wn = Wp, Wn = 2Wp, Wn = Wp/2 and length at selected technology. Carry out the following:

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	i. Set the input signal to a pulse with rise time, fall time of 1ns and pulse width of 10ns and the time period of 20ns and plot the input voltage and output voltage of designed inverter? ii. From the simulation result compute tpHL, tpLH and td for all three geometrical settings of width? iii. Tabulate the results of delay and find the best geometry for minimum delay for CMOS inverter? b) Draw layout of inverter with Wp/Wn = 40/20, use optimum layout methods. Verify for DRC and LVS, extract parasitic and perform post layout simulations, compare the results with pre-layout simulations. Record the observations.
6	a) Capture the schematic of 2-input CMOS NAND gate having similar delay as that of CMOS inverter computed in experiment above. Verify the functionality of NAND gate and also find out the delay td for all four possible combinations of input vectors. Table the results. Increase the drive strength to 2X and 4X and tabulate the results. b) Draw the layout of NAND with Wp/Wn = 40/20, use optimum layout methods. Verify for DRC and LVS, extract parasitic and perform post layout simulations, compare the results with pre-layout simulations. Record the observations.
7	a) Capture schematic of Common Source Amplifier with PMOS Current Mirror Load and find its transient response and AC response? Measure the Unit Gain Bandwidth (UGB), amplification factor by varying transistor geometries, study the impact of variation in width to UGB. b) Draw Layout of common source amplifier, use optimum layout methods. Verify for DRC & LVS, extract parasitic and perform post layout simulations, compare the results with pre-layout simulations. Record the observations.
8	a) Capture schematics of two-stage operational amplifier and measure the following: i. UGB ii. dB Bandwidth iii. Gain Margin and phase margin with and without coupling capacitance iv. Use the op-amp in the inverting and non-inverting configuration and verify its functionality. v. Study the UGB, 3dB bandwidth, gain and power requirement in op-amp by varying the stage wise transistor geometries and record the observations. b) Draw layout of two-stage operational amplifier with minimum transistor width set to 300 (in 180/90/45 nm technology), choose appropriate transistor geometries as per the results obtained in part a. Use optimum layout methods. Verify for DRC and LVS, extract parasitic and perform post layout simulations, compare the results with pre-layout simulations. Record the observations.
	Demonstration Experiments (For CIE)
9	UART • Write Verilog Code • Verify the Functionality using Test-bench • Synthesize the design targeting suitable library and by setting area and timing constraints • Tabulate the Area, Power and Delay for the Synthesized netlist, Identify Critical path
10	For synthesized netlist carry out the following: • Floor planning • Placement and Routing • Record the parameters such as no. of metal layers used for routing, flip method for placement of standard cells • Physical Verification and record the DRC and LVS reports • Generate GDSII

11	Design and characterize 6T binary SRAM cell and measure the following: • Read Time, Write Time, SNM, Power • Draw Layout of 6T SRAM, use optimum layout methods. Verify for DRC & LVS, extract parasitic and perform post layout simulations, compare the results with pre-layout simulations. Record the observations.

Course outcomes (Course Skill Set):

On the completion of this laboratory course, the students will be able to:

1. Design and simulate combinational and sequential digital circuits using Verilog HDL.
2. Understand the synthesis process of digital circuits using EDA tool.
3. Perform ASIC design flow and understand the process of synthesis, synthesis constraints and evaluating the synthesis reports to obtain optimum gate level netlist.
4. Design and simulate basic CMOS circuits like inverter, common source amplifier, differential amplifier, SRAM.
5. Perform RTL_GDSII flow and understand the stages in ASIC design.

Assessment Details (both CIE and SEE)

The weightage of Continuous Internal Evaluation (CIE) is 50% and for Semester End Exam (SEE) is 50%. The minimum passing mark for the CIE is 40% of the maximum marks (20 marks). A student shall be deemed to have satisfied the academic requirements and earned the credits allotted to each course. The student has to secure not less than 35% (18 Marks out of 50) in the semester-end examination (SEE).

Continuous Internal Evaluation (CIE):

CIE marks for the practical course is **50 Marks**.

The split-up of CIE marks for record/ journal and test are in the ratio **60:40**.

- Each experiment to be evaluated for conduction with observation sheet and record write-up. Rubrics for the evaluation of the journal/write-up for hardware/software experiments designed by the faculty who is handling the laboratory session and is made known to students at the beginning of the practical session.
- Record should contain all the specified experiments in the syllabus and each experiment write-up will be evaluated for 10 marks.
- Total marks scored by the students are scaled downed to 30 marks (60% of maximum marks).
- Weightage to be given for neatness and submission of record/write-up on time.
- Department shall conduct 02 tests for 100 marks, the first test shall be conducted after the 8th week of the semester and the second test shall be conducted after the 14th week of the semester.
- In each test, test write-up, conduction of experiment, acceptable result, and procedural knowledge will carry a weightage of 60% and the rest 40% for viva-voce.
- The suitable rubrics can be designed to evaluate each student's performance and learning ability. Rubrics suggested in Annexure-II of Regulation book
- The average of 02 tests is scaled down to **20 marks** (40% of the maximum marks).

The Sum of scaled-down marks scored in the report write-up/journal and average marks of two tests is the total CIE marks scored by the student.

Semester End Evaluation (SEE):

SEE marks for the practical course is 50 Marks.

SEE shall be conducted jointly by the two examiners of the same institute, examiners are appointed by the University

All laboratory experiments are to be included for practical examination.

(Rubrics) Breakup of marks and the instructions printed on the cover page of the answer script to be strictly adhered to by the examiners. **OR** based on the course requirement evaluation rubrics shall be

decided jointly by examiners.

Students can pick one question (experiment) from the questions lot prepared by the internal /external examiners jointly.

Evaluation of test write-up/ conduction procedure and result/viva will be conducted jointly by examiners.

General rubrics suggested for SEE are mentioned here, writeup-20%, Conduction procedure and result in -60%, Viva-voce 20% of maximum marks. SEE for practical shall be evaluated for 100 marks and scored marks shall be scaled down to 50 marks (however, based on course type, rubrics shall be decided by the examiners).

Change of experiment is allowed only once and 15% Marks allotted to the procedure part to be made zero.

The duration of SEE is 03 hours.

Rubrics suggested in Annexure-II of Regulation book

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